TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC7SU04F, TC7SU04FU

### INVERTER

The TC7SU04 is a high speed C2MOS INVERTER fabricated with silicon gate C2MOS technology.

It achieves high speed operation similar to equivalent LSTTL while maintaining the C2MOS low power dissipation.

The internal circuit is composed of single stages inverter, it can be applied for crystal oscillation.

The input is equipped with protection circuits against static discharge or transient excess voltage.

Output currents are 1/2 compared to TC74HC series models.

#### **FEATURES**

•	High Speed	 $t_{pd} = 7ns$ (Typ.	) at
		$V_{CC} = 5V$	

Low Power Dissipation . . . . . . .  $I_{CC} = 1 \mu A$  (Max.) at  $Ta = 25^{\circ} C$ 

High Noise Immunity .....  $V_{NIH} = V_{NIL}$ 

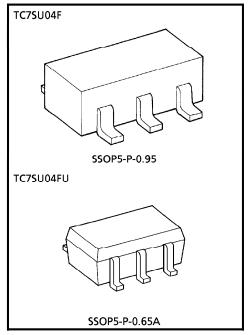
= 28% V<sub>CC</sub> (Min.)

Output Drive Capability ...... 5 LSTTL Loads

Symmetrical Output Impedance ...  $|I_{OH}| = I_{OL}$ = 2mA (Min.)

Balanced Propagation Delays ......  $t_{pLH} = t_{pHL}$ 

Wide Operating Voltage Range ...  $V_{CC(opr)} = 2 \sim 6V$ 

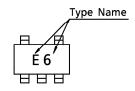


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A: 0.006g (Typ.)

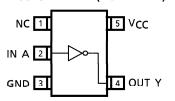
# **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	V <sub>IN</sub>	-0.5~V <sub>CC</sub> +0.5	V
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> + 0.5	٧
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 12.5	mA
DC V <sub>CC</sub> / Ground Current	Icc	± 25	mA
Power Dissipation	PD	200	mW
Storage Temperature	T <sub>stg</sub>	<b>-65∼150</b>	°C
Lead Temperature (10s)	TL	260	°C

#### **MARKING**

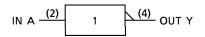


#### PIN ASSIGNMENT (TOP VIEW)



TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

#### **LOGIC DIAGRAM**



#### **RECOMMENDED OPERATING CONDITIONS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~6	V
Input Voltage	VIN	0~V <sub>CC</sub>	V
Output Voltage	Vout	0~V <sub>CC</sub>	٧
Operating Temperature	T <sub>opr</sub>	- 40~85	°C

#### DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = -4	l0∼85°C	UNIT
CHARACTERISTIC	3 T IVIBOL			Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	OIVII
High-Level	V <sub>IH</sub>			2.0	1.7	-	_	1.7	_	
Input Voltage				4.5	3.6	—	—	3.6	—	V
input voitage				6.0	4.8	_		4.8	_	
Low-Level				2.0	_	_	0.3	_	0.3	
Input Voltage	VIL		_	4.5	—	—	0.9	<u> </u>	0.9	V
input voitage				6.0	_	_	1.2	_	1.2	
	Voн	V <sub>IN</sub> = V <sub>IL</sub>		2.0	1.8	2.0	—	1.8	<b>—</b>	
Liberta Lavel			$I_{OH} = -20\mu A$	4.5	4.0	4.5	—	4.0	_	
High-Level				6.0	5.5	5.9	<u> </u>	5.5	<u> </u>	J v
Output Voltage			$I_{OH} = -2mA$	4.5	4.18	4.31	_	4.13	_	
			$I_{OH} = -2.6mA$	6.0	5.68	5.80	_	5.63	_	
	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub>		2.0	_	0.0	0.2	_	0.2	
Lave Lavel			$I_{OL} = 20 \mu A$	4.5	—	0.0	0.2	<b> </b>	0.5	
Low-Level				6.0	_	0.0	0.5	_	0.5	V
Output Voltage			$I_{OL} = 2mA$	4.5	_	0.17	0.26		0.33	
			$I_{OL} = 2.6 mA$	6.0	_	0.18	0.26	_	0.33	
Input Leakage Current	IN	V <sub>IN</sub> = V <sub>CC</sub>	or GND	6.0	_	_	± 0.1	_	± 1.0	
Quiescent Supply Current	<sup>l</sup> cc	V <sub>IN</sub> = V <sub>CC</sub> (	or GND	6.0	_	_	1.0	_	10.0	μΑ

Output currents are 1/2 compared to TC74HC series models.

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AC ELECTRICAL CHARACTERISTICS (C <sub>L</sub> = 15p	oF, Input $t_r = t_f = 6$ ns, $V_{CC} = 5V$ )
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CHARACTERISTIC	SYMBOL	TEST CONDITION	Т	UNIT		
CHARACTERISTIC	STIVIBUL	TEST CONDITION	MIN.	TYP.	MAX.	UNII
Output Transition	tTLH			5	10	ns
Time	tTHL	_			10	113
Propagation Delay	t <sub>pLH</sub>			7	15	nc
Time	t <sub>pHL</sub>	_		_ ′	13	ns

## AC ELECTRICAL CHARACTERISTICS ( $C_L = 50pF$ , Input $t_r = t_f = 6ns$ )

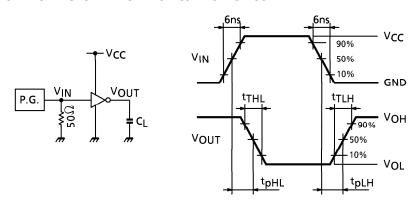
CHARACTERISTIC	SYMBOL	TEST CONDITION		Т	a = 25°	C.	Ta = -4	UNIT	
CHARACTERISTIC	STIVIBUL	TEST CONDITION		MIN.	TYP.	MAX.	MIN.		MAX.
Output Transition	t		2.0	_	50	125	_	155	
Time	t <sub>TLH</sub>	<u> </u>	4.5	_	14	25	_	31	ns
Time	t <sub>THL</sub>		6.0	_	12	21	_	26	
Propagation Delay	n Dolay t		2.0	_	48	100	_	125	
Time	t <sub>pLH</sub>	<del></del>	4.5	<u> </u>	12	20	<u> </u>	25	ns
Time	t <sub>pHL</sub>		6.0	_	9	17	_	21	
Input Capacitance	CIN	_		_	5	10	_	10	
Power Dissipation Capacitance	C <sub>PD</sub>	(Note 1)		_	10	_			pF

Note 1: CpD defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

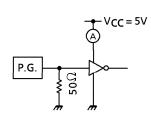
Average operating current can be obtained by the equation hereunder.

ICC (opr) = CPD·VCC·fIN + ICC

#### **SWITCHING CHARACTERISTICS TEST CIRCUIT**



# ICC (opr) TEST CIRCUIT



Input waveform is the same as that in case of switching characteristics test.